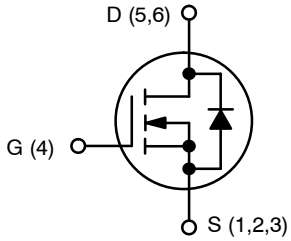
# MOSFET – Power, Single N-Channel

## 80 V, 20.7 mΩ, 32 A

# NVMFS6H858N

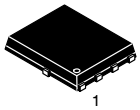
| $V_{(BR)DSS}$ | $R_{DS(ON)}$ MAX | $I_D$ MAX |
|---|---|---|
| 80 V | 20.7 mΩ @ 10 V | 32 A |



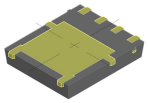

N−CHANNEL MOSFET

### Features

- Small Footprint (5x6 mm) for Compact Design
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low $Q_G$ and Capacitance to Minimize Driver Losses
- NVMFS6H858NWF − Wettable Flank Option for Enhanced Optical Inspection
- AEC−Q101 Qualified and PPAP Capable
- These Devices are Pb−Free and are RoHS Compliant




DFN5
(SO−8FL)
CASE 488AA
STYLE 1



DFNW5
(FULL−CUT SO8FL WF)
CASE 507BA

### MAXIMUM RATINGS ($T_J$ = 25°C unless otherwise noted)

| Parameter | | | Symbol | Value | Unit |
|---|---|---|---|---|---|
| Drain−to−Source Voltage | | | $V_{DSS}$ | 80 | V |
| Gate−to−Source Voltage | | | $V_{GS}$ | ±20 | V |
| Continuous Drain Current $R_{\theta JC}$ (Notes 1, 3) | Steady State | $T_C$ = 25°C | $I_D$ | 29 | A |
| | | $T_C$ = 100°C | | 21 | |
| Power Dissipation $R_{\theta JC}$ (Note 1) | | $T_C$ = 25°C | $P_D$ | 42 | W |
| | | $T_C$ = 100°C | | 21 | |
| Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2, 3) | Steady State | $T_A$ = 25°C | $I_D$ | 8.4 | A |
| | | $T_A$ = 100°C | | 6.0 | |
| Power Dissipation $R_{\theta JA}$ (Notes 1, 2) | | $T_A$ = 25°C | $P_D$ | 3.5 | W |
| | | $T_A$ = 100°C | | 1.8 | |
| Pulsed Drain Current | $T_A$ = 25°C, $t_p$ = 10 μs | | $I_{DM}$ | 137 | A |
| Operating Junction and Storage Temperature Range | | | $T_J$, $T_{stg}$ | −55 to +175 | °C |
| Source Current (Body Diode) | | | $I_S$ | 35 | A |
| Single Pulse Drain−to−Source Avalanche Energy ($I_{L(pk)}$ = 3.5 A) | | | $E_{AS}$ | 151 | mJ |
| Lead Temperature for Soldering Purposes (1/8″ from case for 10 s) | | | $T_L$ | 260 | °C |

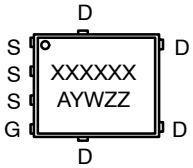
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### THERMAL RESISTANCE MAXIMUM RATINGS

| Parameter | Symbol | Value | Unit |
|---|---|---|---|
| Junction−to−Case − Steady State | $R_{\theta JC}$ | 3.5 | °C/W |
| Junction−to−Ambient − Steady State (Note 2) | $R_{\theta JA}$ | 42.5 | |

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface−mounted on FR4 board using a 650 $mm^2$, 2 oz. Cu pad.
3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.

### MARKING DIAGRAM




XXXXXX = 6H858N (NVMFS6H858N) or 858NWF (NVMFS6H858NWF)
A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

### ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 5 of this data sheet.

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**ELECTRICAL CHARACTERISTICS** ($T_J$ = 25°C unless otherwise specified)

| Parameter | Symbol | Test Condition | | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|---|
| **OFF CHARACTERISTICS** | | | | | | | |
| Drain−to−Source Breakdown Voltage | $V_{(BR)DSS}$ | $V_{GS}$ = 0 V, $I_D$ = 250 μA | | 80 | | | V |
| Drain−to−Source Breakdown Voltage Temperature Coefficient | $V_{(BR)DSS}/T_J$ | | | | 44 | | mV/°C |
| Zero Gate Voltage Drain Current | $I_{DSS}$ | $V_{GS}$ = 0 V, $V_{DS}$ = 80 V | $T_J$ = 25 °C | | | 10 | μA |
| | | | $T_J$ = 125°C | | | 250 | |
| Gate−to−Source Leakage Current | $I_{GSS}$ | $V_{DS}$ = 0 V, $V_{GS}$ = 20 V | | | | 100 | nA |
| **ON CHARACTERISTICS** (Note 4) | | | | | | | |
| Gate Threshold Voltage | $V_{GS(TH)}$ | $V_{GS}$ = $V_{DS}$, $I_D$ = 30 μA | | 2.0 | | 4.0 | V |
| Threshold Temperature Coefficient | $V_{GS(TH)}/T_J$ | | | | −7.5 | | mV/°C |
| Drain−to−Source On Resistance | $R_{DS(on)}$ | $V_{GS}$ = 10 V | $I_D$ = 5 A | | 16.9 | 20.7 | mΩ |
| Forward Transconductance | $g_{FS}$ | $V_{DS}$ =15 V, $I_D$ = 10 A | | | 36 | | S |
| **CHARGES, CAPACITANCES & GATE RESISTANCE** | | | | | | | |
| Input Capacitance | $C_{ISS}$ | $V_{GS}$ = 0 V, f = 1 MHz, $V_{DS}$ = 40 V | | | 510 | | pF |
| Output Capacitance | $C_{OSS}$ | | | | 80 | | |
| Reverse Transfer Capacitance | $C_{RSS}$ | | | | 4.7 | | |
| Total Gate Charge | $Q_{G(TOT)}$ | $V_{GS}$ = 10 V, $V_{DS}$ = 40 V; $I_D$ = 10 A | | | 8.9 | | nC |
| Threshold Gate Charge | $Q_{G(TH)}$ | $V_{GS}$ = 10 V, $V_{DS}$ = 40 V; $I_D$ = 10 A | | | 2.2 | | |
| Gate−to−Source Charge | $Q_{GS}$ | | | | 2.8 | | |
| Gate−to−Drain Charge | $Q_{GD}$ | | | | 1.7 | | |
| Plateau Voltage | $V_{GP}$ | | | | 4.8 | | V |
| **SWITCHING CHARACTERISTICS** (Note 5) | | | | | | | |
| Turn−On Delay Time | $t_{d(ON)}$ | $V_{GS}$ = 10 V, $V_{DS}$ = 64 V, $I_D$ = 10 A, $R_G$ = 2.5 Ω | | | 8.0 | | ns |
| Rise Time | $t_r$ | | | | 17 | | |
| Turn−Off Delay Time | $t_{d(OFF)}$ | | | | 19 | | |
| Fall Time | $t_f$ | | | | 13 | | |
| **DRAIN−SOURCE DIODE CHARACTERISTICS** | | | | | | | |
| Forward Diode Voltage | $V_{SD}$ | $V_{GS}$ = 0 V, $I_S$ = 5 A | $T_J$ = 25°C | | 0.8 | 1.2 | V |
| | | | $T_J$ = 125°C | | 0.7 | | |
| Reverse Recovery Time | $t_{RR}$ | $V_{GS}$ = 0 V, dIS/dt = 100 A/μs, $I_S$ = 10 A | | | 29 | | ns |
| Charge Time | $t_a$ | | | | 19 | | |
| Discharge Time | $t_b$ | | | | 9.0 | | |
| Reverse Recovery Charge | $Q_{RR}$ | | | | 23 | | nC |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
5. Switching characteristics are independent of operating junction temperatures.

## TYPICAL CHARACTERISTICS

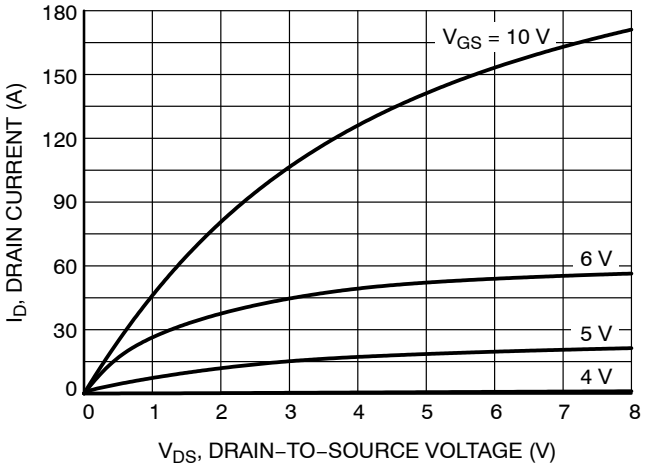



**Figure 1. On−Region Characteristics**

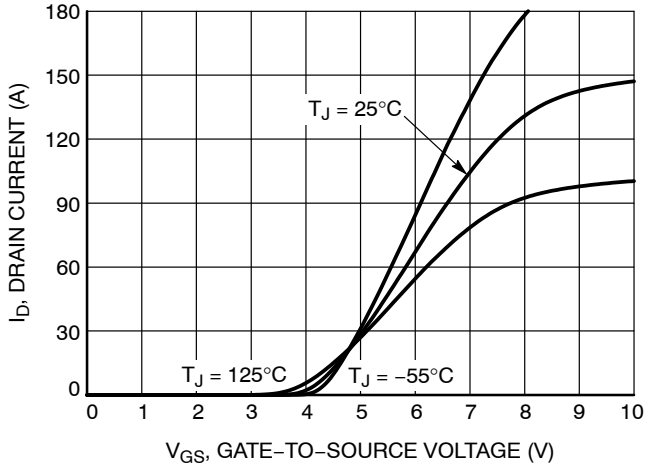



**Figure 2. Transfer Characteristics**

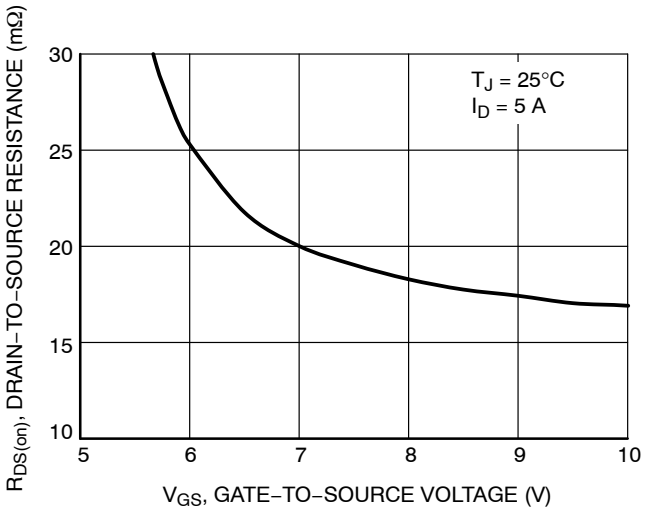



**Figure 3. On−Resistance vs. Gate−to−Source Voltage**

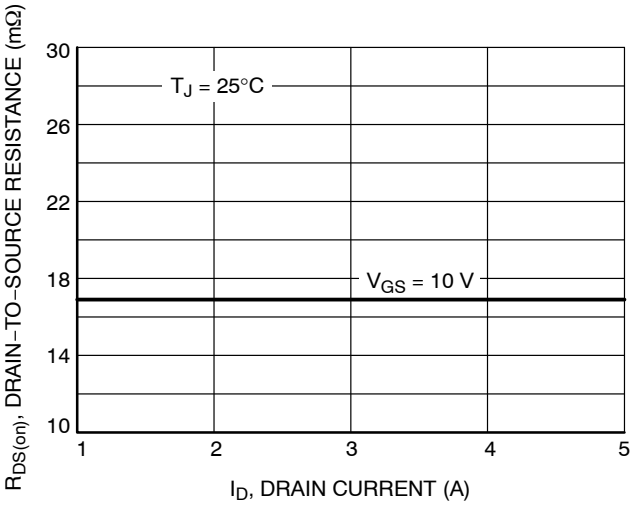



**Figure 4. On−Resistance vs. Drain Current and Gate Voltage**

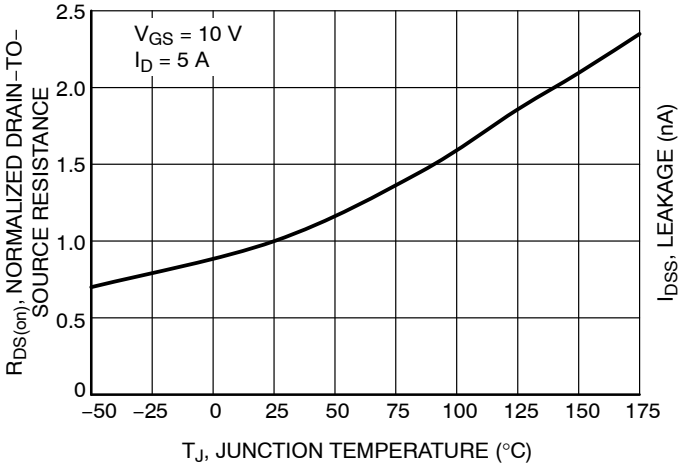



**Figure 5. On−Resistance Variation with Temperature**

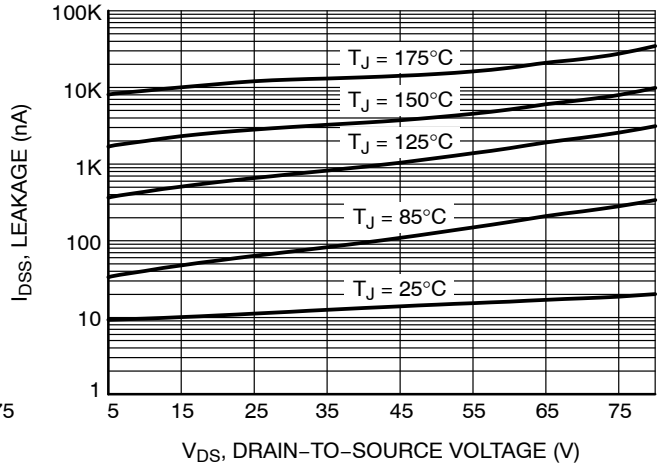



**Figure 6. Drain−to−Source Leakage Current vs. Voltage**

## TYPICAL CHARACTERISTICS (Continued)

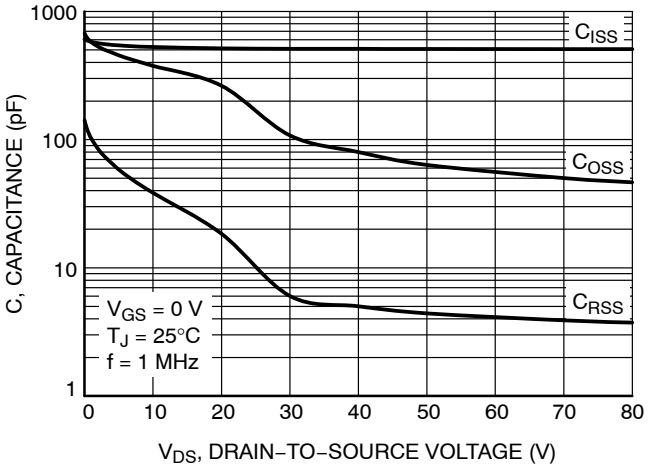



**Figure 7. Capacitance Variation**

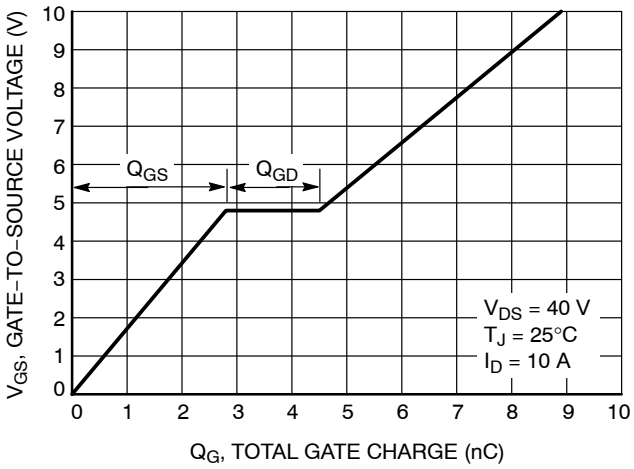



**Figure 8. Gate−to−Source Voltage vs. Total Charge**

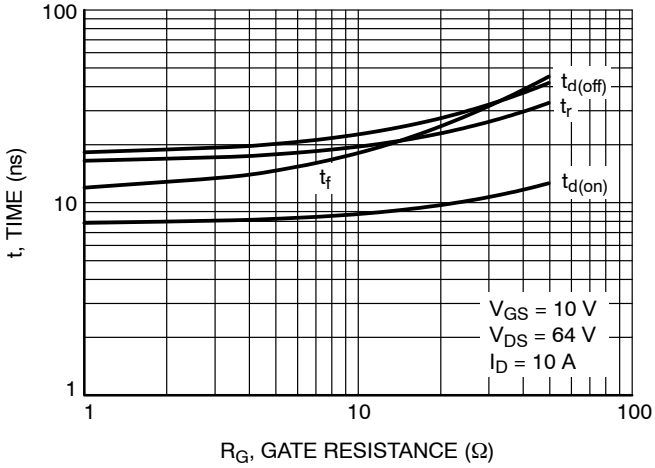



**Figure 9. Resistive Switching Time Variation vs. Gate Resistance**

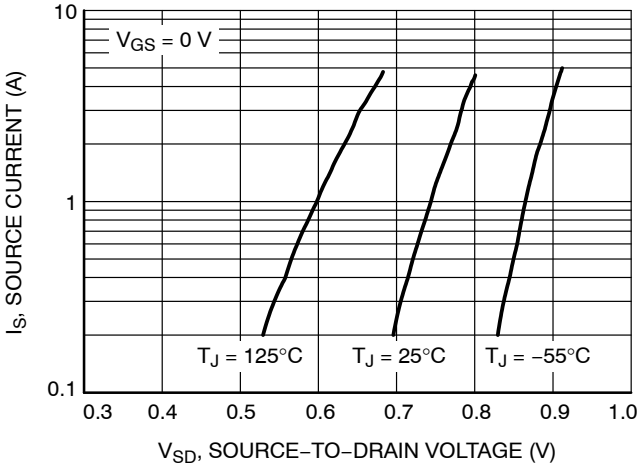



**Figure 10. Diode Forward Voltage vs. Current**

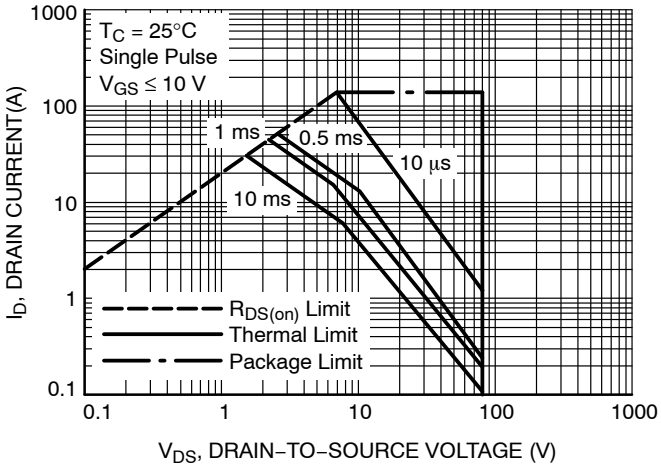



**Figure 11. Maximum Rated Forward Biased Safe Operating Area**

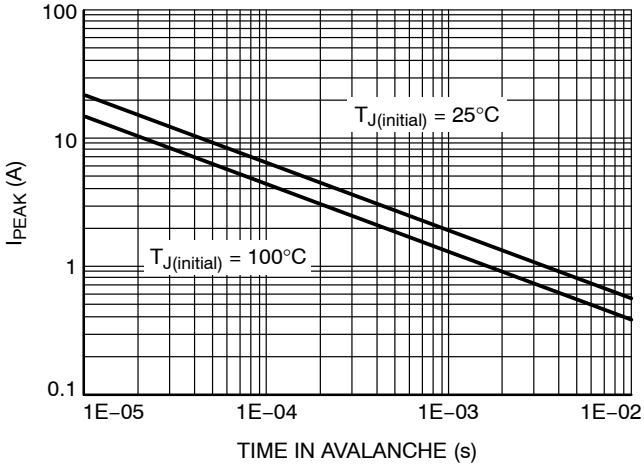



**Figure 12. $I_{PEAK}$ vs. Time in Avalanche**

## TYPICAL CHARACTERISTICS (Continued)

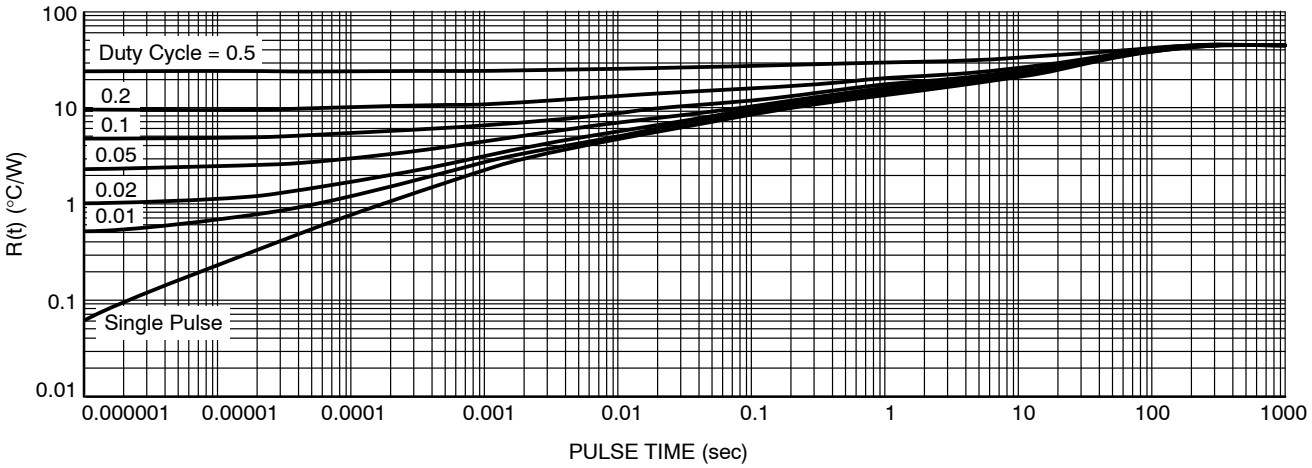
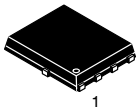



**Figure 13. Thermal Characteristics**

### DEVICE ORDERING INFORMATION

| Device | Marking | Package | Shipping† |
|---|---|---|---|
| NVMFS6H858NT1G | 6H858N | DFN5<br>(Pb−Free) | 1500 / Tape & Reel |
| NVMFS6H858NWFT1G | 858NWF | DFNW5<br>(Pb−Free, Wettable Flanks) | 1500 / Tape & Reel |

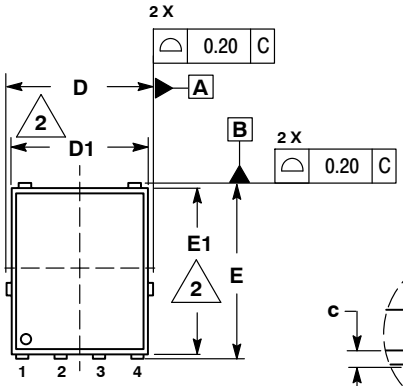
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



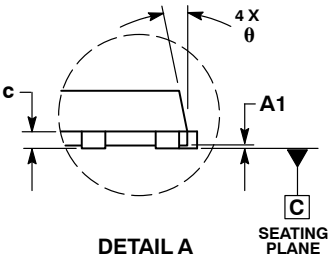
SCALE 2:1

**DFN5 5x6, 1.27P**
**(SO−8FL)**
CASE 488AA
ISSUE N

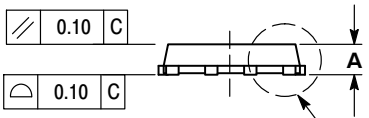
DATE 25 JUN 2018




TOP VIEW




DETAIL A



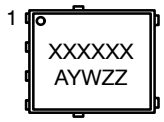

SIDE VIEW

DETAIL A

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

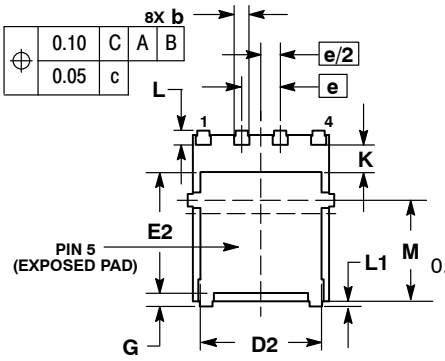
| DIM | MILLIMETERS | | |
|---|---|---|---|
| | MIN | NOM | MAX |
| A | 0.90 | 1.00 | 1.10 |
| A1 | 0.00 | ––– | 0.05 |
| b | 0.33 | 0.41 | 0.51 |
| c | 0.23 | 0.28 | 0.33 |
| D | 5.00 | 5.15 | 5.30 |
| D1 | 4.70 | 4.90 | 5.10 |
| D2 | 3.80 | 4.00 | 4.20 |
| E | 6.00 | 6.15 | 6.30 |
| E1 | 5.70 | 5.90 | 6.10 |
| E2 | 3.45 | 3.65 | 3.85 |
| e | 1.27 BSC | | |
| G | 0.51 | 0.575 | 0.71 |
| K | 1.20 | 1.35 | 1.50 |
| L | 0.51 | 0.575 | 0.71 |
| L1 | 0.125 REF | | |
| M | 3.00 | 3.40 | 3.80 |
| θ | 0 ° | ––– | 12 ° |

## GENERIC MARKING DIAGRAM*



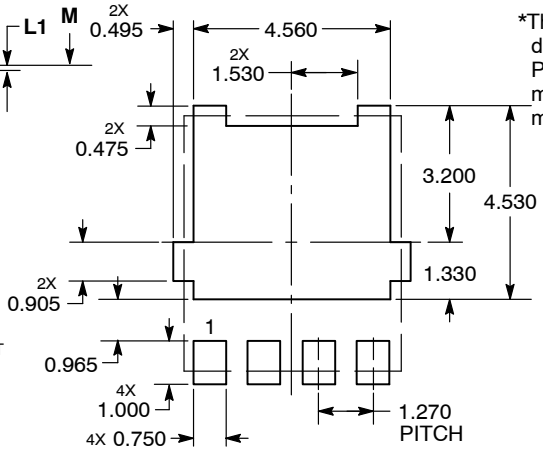

XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present. Some products may not follow the Generic Marking.




BOTTOM VIEW

## RECOMMENDED SOLDERING FOOTPRINT*




DIMENSIONS: MILLIMETERS

STYLE 1:
PIN 1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN

STYLE 2:
PIN 1. ANODE
2. ANODE
3. ANODE
4. NO CONNECT
5. CATHODE

*For additional information on our Pb−Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

| DOCUMENT NUMBER: | 98AON14036D | Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red. |
|---|---|---|
| DESCRIPTION: | DFN5 5x6, 1.27P (SO−8FL) | PAGE 1 OF 1 |

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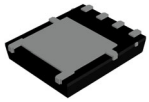
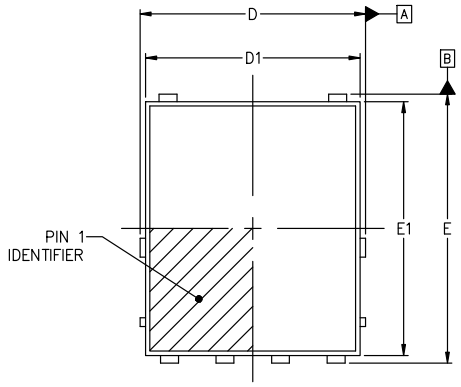
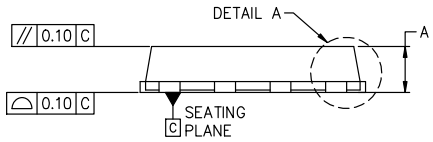


**DFNW5 4.90x5.90x1.00, 1.27P**
CASE 507BA
ISSUE C

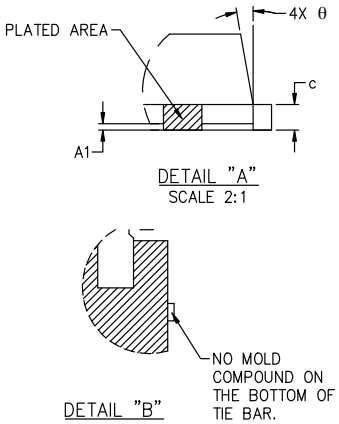
DATE 19 SEP 2024




TOP VIEW




SIDE VIEW



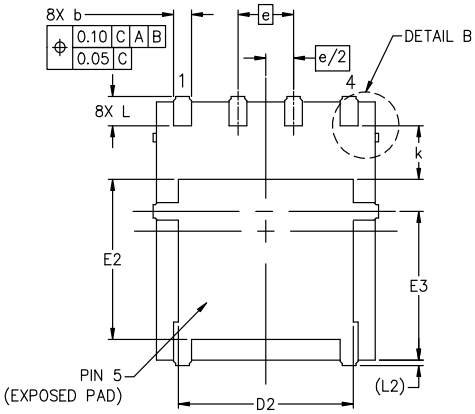

DETAIL "A"
SCALE 2:1

DETAIL "B"
SCALE 2:1

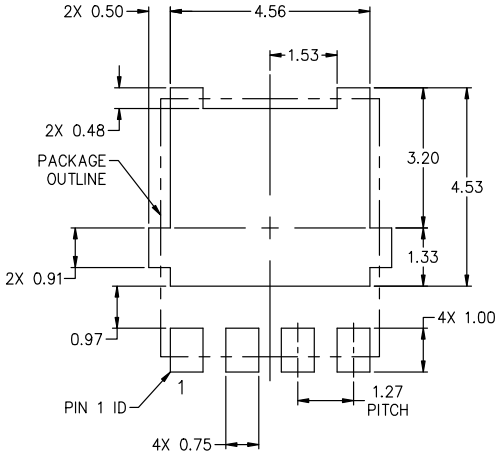
NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5M−2018.
2. ALL DIMENSIONS ARE IN MILLIMETERS.
3. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
4. THIS PACKAGE CONTAINS WETTABLE FLANK DESIGN FEATURES TO AID IN FILLET FORMATION ON THE LEADS DURING MOUNTING.

| DIM | MILLIMETERS | | |
|---|---|---|---|
| | MIN | NOM | MAX |
| A | 0.90 | 1.00 | 1.10 |
| A1 | 0.00 | --- | 0.05 |
| b | 0.33 | 0.41 | 0.51 |
| c | 0.23 | 0.28 | 0.33 |
| D | 5.00 | 5.15 | 5.30 |
| D1 | 4.70 | 4.90 | 5.10 |
| D2 | 3.80 | 4.00 | 4.20 |
| E | 6.00 | 6.15 | 6.30 |
| E1 | 5.70 | 5.90 | 6.10 |
| E2 | 3.45 | 3.65 | 3.85 |
| E3 | 3.00 | 3.40 | 3.80 |
| e | 1.27 BSC | | |
| k | 1.20 | 1.35 | 1.50 |
| L | 0.51 | 0.57 | 0.71 |
| L2 | 0.15 REF. | | |
| θ | 0° | 6° | 12° |

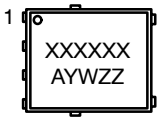



BOTTOM VIEW




RECOMMENDED MOUNTING FOOTPRINT*
*FOR ADDITIONAL INFORMATION ON OUR Pb−FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

**GENERIC MARKING DIAGRAM***




XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot " ▪", may or may not be present. Some products may not follow the Generic Marking.

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|---|---|---|
| DESCRIPTION: | DFNW5 4.90x5.90x1.00, 1.27P | PAGE 1 OF 1 |

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